

Description:

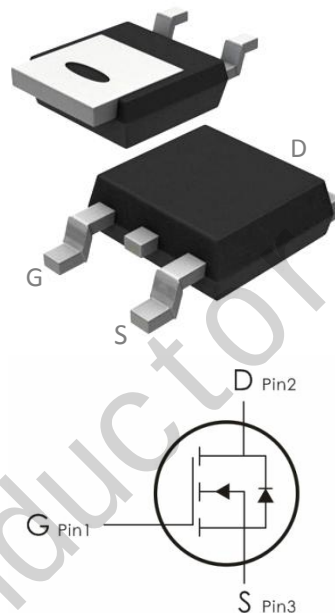
This N-Channel MOSFET uses advanced SGT technology and

design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=100V, I_D=36A, R_{DS(on)}<20m\Omega @V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current ¹⁾ , $T_C=25^\circ C$	36	A
$I_{D, pulse}$	Pulsed drain current ²⁾ , $T_C=25^\circ C$	90	A
P_D	Power dissipation ³⁾ , $T_C=25^\circ C$	71	W
E_{AS}	Single pulsed avalanche energy ⁵⁾	57	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.76	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient ⁴⁾	62	

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	100	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =100V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	1.4	---	2.5	V
R _{DS(ON)}	Drain-Source On Resistance	V _{GS} =10V, I _D =10A	---	13.8	20	m Ω
		V _{GS} =4.5V, I _D =7A	---	17.4	26	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =50V, V _{GS} =0V, f=100KHz	---	1000	---	pF
C _{oss}	Output Capacitance		---	180	---	
C _{rss}	Reverse Transfer Capacitance		---	9.5	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =50V, I _D =5A, V _{GS} =10V, R _G =10Ω	---	16.6	--	ns
t _r	Rise Time		---	3.8	---	ns
t _{d(off)}	Turn-Off Delay Time		---	75.5	---	ns
t _f	Fall Time		---	46	---	ns
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =50V, I _D =5A	---	16.2	---	nC
Q _{gs}	Gate-Source Charge		---	2.8	---	nC
Q _{gd}	Gate-Drain Charge		---	4.1	---	nC
V _{plateau}	Gate plateau voltage		---	3	---	V
Drain-Source Diode Characteristics						
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V, I _S =12A	---	---	1.3	V

trr	Reverse Recovery Time	$V_R=50\text{ V}, I_S=5\text{ A},$ $di/dt=100\text{ A}/\mu\text{ s}$	---	49	---	Ns
qrr	Reverse Recovery Charge		---	61.8	---	nc
I_{rrm}	Peak reverse recovery current		---	2.4	---	A

Notes:

- 1) Calculated continuous current based on maximum allowable junction temperature.
- 2) Repetitive rating; pulse width limited by max. junction temperature.
- 3) Pd is based on max. junction temperature, using junction-case thermal resistance.
- 4) The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a=25^\circ\text{C}$.
- 5) $V_{DD}=50\text{ V}, V_{GS}=10\text{ V}, L=0.3\text{ mH}$, starting $T_J=25^\circ\text{C}$.

Typical Characteristics: ($T_c=25^\circ\text{C}$ unless otherwise noted)

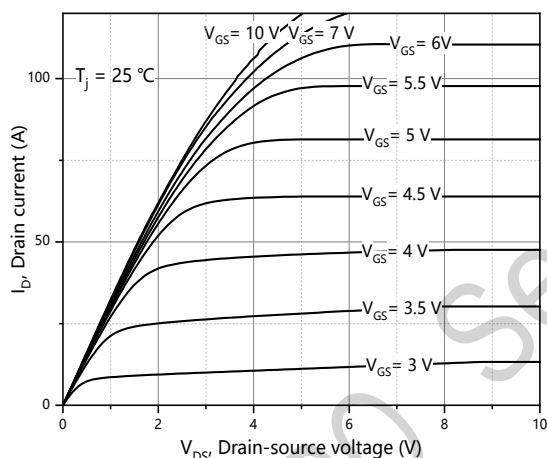


Figure 1. Typ. output characteristics

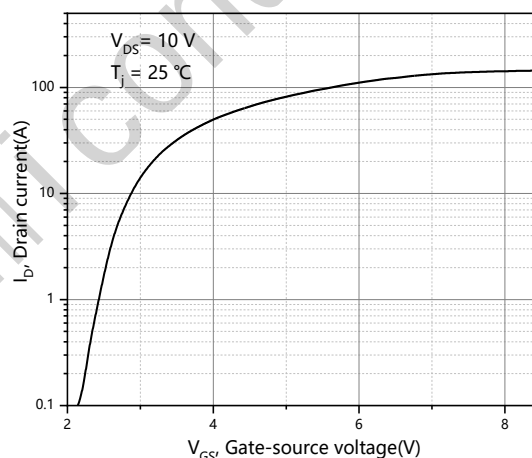


Figure 2. Typ. transfer characteristics

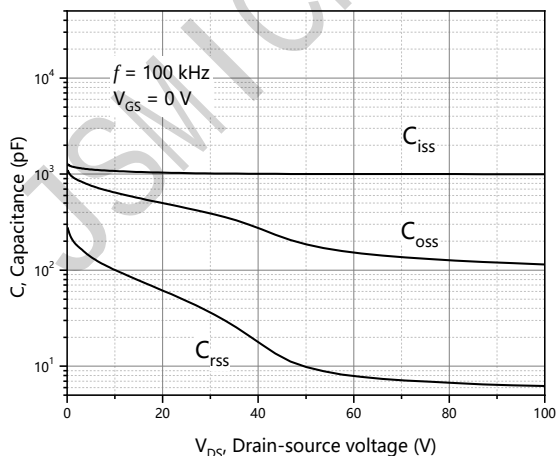


Figure 3. Typ. capacitances

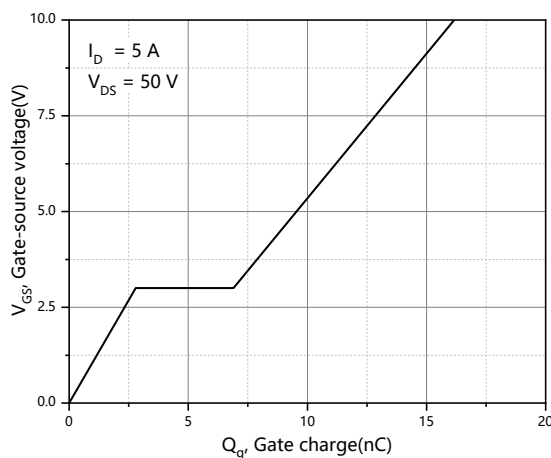
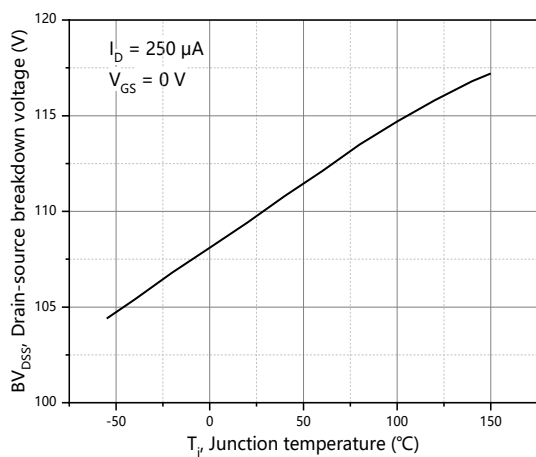
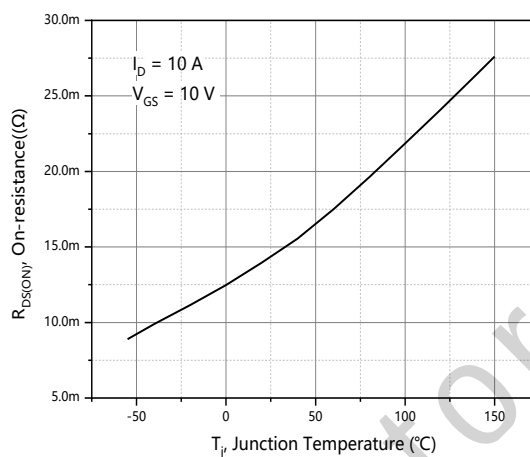
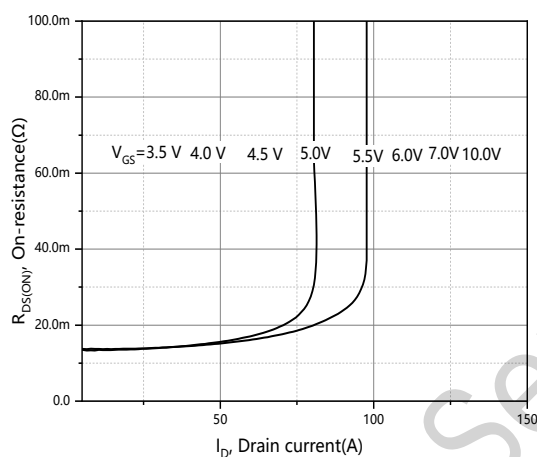
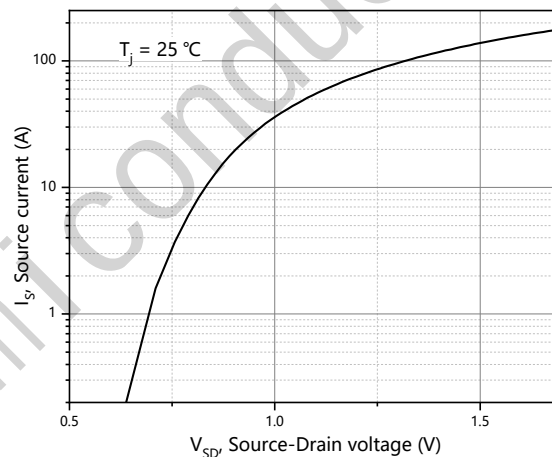
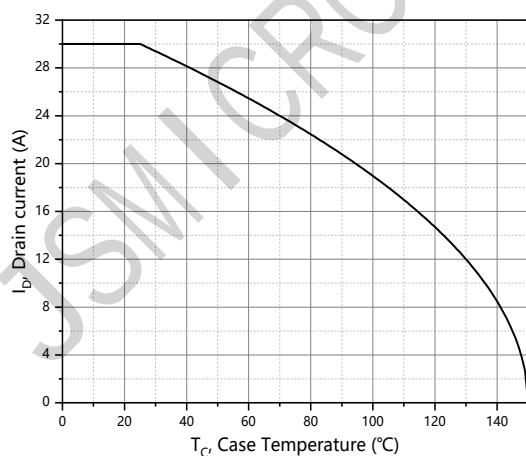
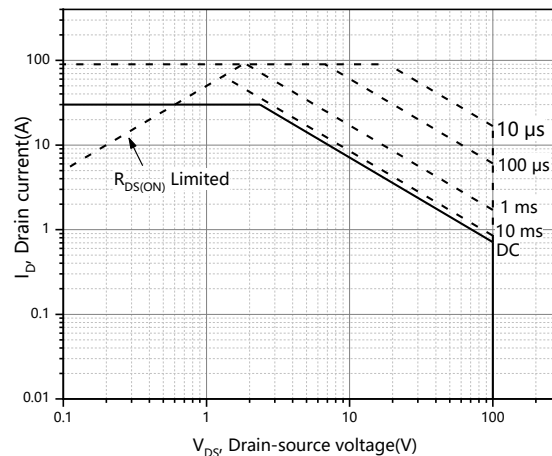


Figure 4. Typ. gate charge


Figure 5. Drain-source breakdown voltage

Figure 6. Drain-source on-state resistance

Figure 7. Drain-source on-state resistance

Figure 8. Forward characteristic of body diode

Figure 9. Drain current

Figure 10. Safe operation area $T_C=25\text{ }^{\circ}\text{C}$

外形尺寸图 / Package Dimensions

